



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

SASHIDA et al.

Serial Number: 09/321,605

Group Art Unit: 2813

Filed: May 28, 1999

Examiner: J. Chen

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING CAPACITOR

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

February 15, 2002

Sir:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 21 as follows:

1. (Thrice Amended) A method of manufacturing a semiconductor device comprising
the steps of :

forming a couple of impurity diffusion layers in a semiconductor substrate;

forming a first insulating film covering the semiconductor substrate;

forming a lower electrode of a capacitor on the first insulating film;

forming an oxide dielectric film of the capacitor on the lower electrode;

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